CLAIM AMENDMENTS

1. (Amended.) A ~~magnetic substance~~ thin film electromagnetic interference suppressor of a magnetic composition comprising M, X and Y, wherein M is a metallic magnetic material selected from the group consisting of Fe, Co, Ni, and two or more thereof, X being an element or elements other than M and Y, and Y being selected from the group consisting of F, N, and two or more thereof, ~~which is characterized in that~~ wherein said M-X-Y magnetic composition has a concentration of M in the composition so that said M-X-Y magnetic composition has a saturation magnetization of 35-80% of that of the metallic bulk of magnetic material comprising M alone, said magnetic composition having the maximum μ''_{max} of complex permeability μ'' in a frequency range of 0.1-10 gigahertz (GHz).

Claim 2 – cancelled.

3. (Amended.) The ~~magnetic substance~~ suppressor according to claim ~~2~~1, said metallic magnetic material ~~X~~ M having a saturation magnetization, wherein said magnetic composition has a saturation magnetization which is 60-80% of the saturation magnetization of the metallic magnetic material ~~X~~ M.

4. (Amended.) The ~~magnetic substance~~ suppressor according to claim ~~2~~ 3, wherein said magnetic composition has a DC specific resistance of 100-700 $\mu\Omega \cdot cm$.

Claim 5 – cancelled.

6. (Amended.) The ~~magnetic substance~~ suppressor according to claim ~~5~~1, said metallic magnetic material ~~X~~ M having a saturation magnetization, wherein said magnetic composition has a saturation magnetization which is 35-60% of the saturation magnetization of the metallic magnetic material ~~X~~ M.

7. (Amended.) The ~~magnetic substance~~ suppressor according to claim ~~6~~5, wherein said magnetic composition has a DC specific resistance of 500 $\mu\Omega \cdot cm$ or more.

8. (Amended.) The ~~magnetic substance~~ suppressor according to claim 1, wherein X is selected from the group consisting of C, Bi, Si, Al, Mg, Ti, Zn, Hf, Sr, Nb, Ta, rare-earth metals, and two or more thereof.

9. (Amended.) The ~~magnetic substance~~ suppressor according to claim 1, wherein said metallic magnetic material M is distributed as granular grains in a matrix composition consisting of X and Y.

Claims 10-11 – cancelled.

12. (Amended.) The ~~magnetic substance~~ suppressor according to claim 8, wherein said magnetic composition is an Fe-Al-O composition ~~represented by a formula of Fe_{α}-Si_{β}-O_{γ}~~.

13. (Withdrawn.) The magnetic substance according to any one of claims 1-11, wherein said magnetic composition is a composition represented by a formula of Fe_{α}-Si_{β}-O_{γ}.

14. (Amended.) The ~~magnetic substance~~ suppressor according to claim 1, wherein said magnetic composition is a thin film formed by sputtering process.

15. (Withdrawn.) The magnetic substance according to any one of claims 1-13, wherein said magnetic composition is a thin film formed by vapor deposition process.

16. (Withdrawn.) The magnetic substance according to any one of claims 1-15, which is formed as a plate having a thickness of 0.3-20 μ.cm for use as a high frequency noise suppressor.

17. (Withdrawn.) A method for suppressing a high frequency noise from flowing in a circuit line in an electronic device characterized by disposing said plate of claim 16 adjacent to, or directly onto said electronic device.

18. (New.) The suppressor according to claim 3, which has a complex permeability frequency response of a frequency band where a relative bandwidth bwr is 191% or less, said relative bandwidth bwr is determined as a percentage ratio of bandwidth between two frequency points which show the complex permeability as a half value μ''_{so} of the maximum μ''_{max} to the center frequency of said bandwidth.

19. (New.) The suppressor according to claim 6, which has a comlex permeablity frequency response of a frequency band where a relative bandwidth bwr is 148% or more, said relative bandwidth bwr is determined as a percentage ratio of bandwidth between two frequency points which shows the complex

permeability as a half value μ''_{50} of the maximum μ''_{max} to the center frequency of said bandwidth.